VRW056 ṂṂ Ŀ SQS ӕṀ ҷ s ǁ ⅂ Silicon PNP transistor in a SOT-23 Plastic Package.

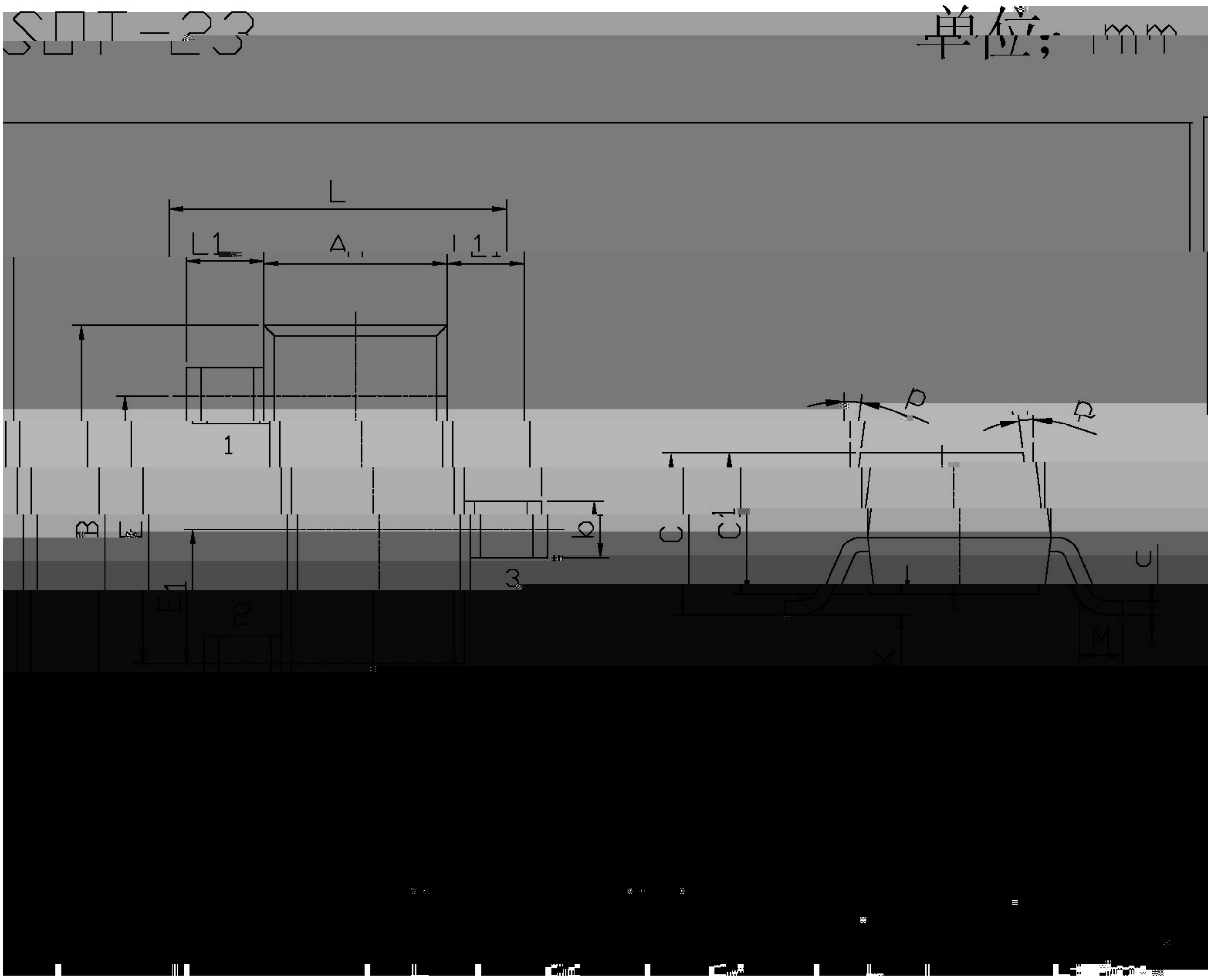
ϫ ↄ ╙ պ ` ɩ Ḩ $V_{CE(sat)}$
High current gain, Low collector-emitter saturation voltage.

[illegible]

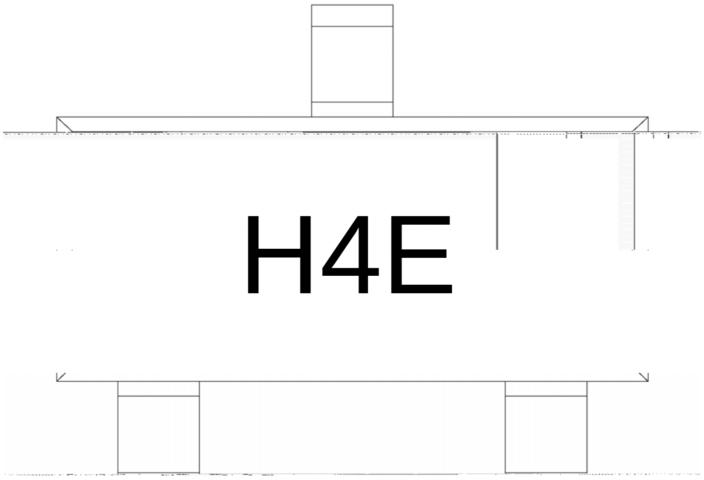
v Ώ Parameter	ɏ ᴺ Symbol	Ώ Ө Rating	ᴅ Ʉ Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v Ώ Parameter	ɏ ᴺ Symbol	╜ ꜝ᛫ Ʈ Test Conditions	ῳ ṇ Ө Min	Ɛ ʒ Ө Typ	ῳ ᵶ Ө Max	ᴅ Ʉ Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	I_CC I	E		O	

/ Package Dimensions



/ Marking Instructions



ب ˝ χ

K χ ҥ ʒ ᴎ Ҧ

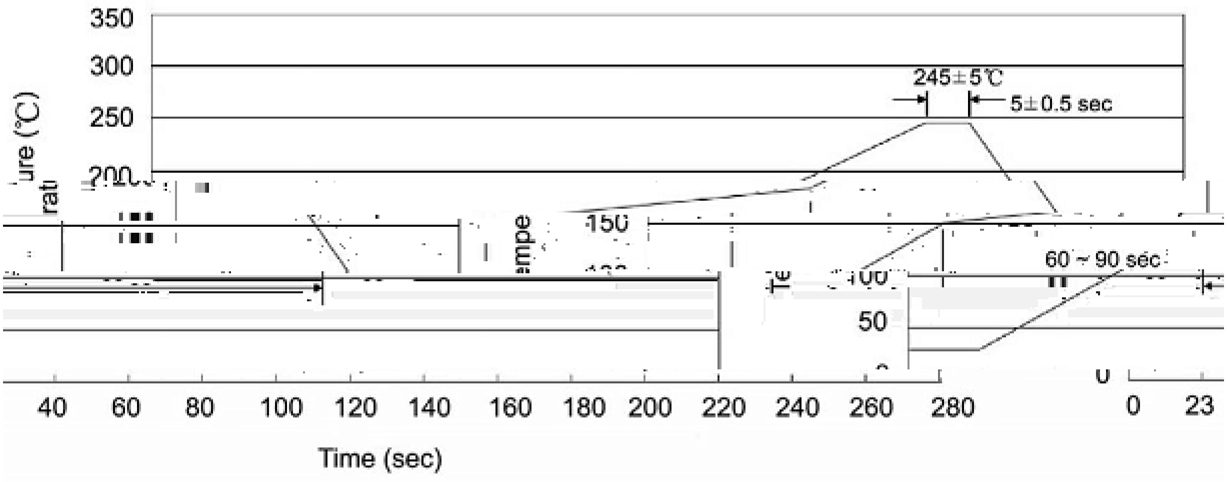
7H χ ҥ ʒ ᴺ Ҧ

Note:

H: Company Code.

4E: Product Type Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı ˋH ڗ 60 Ḱ 90sec;

2 Š Ӫ □ ẙ 245 ° 5 ɫ ı ˋH ڗ ˋY ϰ 㓇 5 ° 0.5sec;

3 ì ˙ ˥ ˛ כ ಹ ẙ 㓇 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ẙ χ 260±5 ˋH ڗ χ 10±1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ᦱ ˋ ɣ ᒷ / REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices